

Separate Summary Sheet

Product Specifications of the 8th-Generation G8H IGBT Series

**650V products**

Item	Specifications	
Renesas Part No.	RBN40H65T1GPQ-A0 (40A) RBN50H65T1GPQ-A0 (50A) RBN75H65T1GPQ-A0 (75A)	
Order Part No.	RBN40H65T1GPQ-A0#T2 RBN50H65T1GPQ-A0#T2 RBN75H65T1GPQ-A0#T2	
Collector to emitter voltage VCES	650 V	
Gate to emitter voltage VGES	+/- 30 V	
Collector current IC	Tc = 25 °C	80 A, 100A, 150A
	Tc = 100 °C	40 A, 50A, 75A
Junction temperature Tj	175 °C	
Collector to emitter saturation voltage VCE(sat)	1.5 V	
Gate to emitter cutoff voltage VGE (off)	5.0 - 6.8 V	
Package Information	TO-247	

**1250V products**

Item	Specifications	
Renesas Part Name	RBN25H125S1GPQ-A0 (25A) RBN40H125S1GPQ-A0 (40A) RBN75H125S1GP4-A0 (75A)	
Order Part Name	RBN25H125S1GPQ-A0#T2 RBN40H125S1GPQ-A0#T2 RBN75H125S1GP4-A0#T2	
Collector to emitter voltage VCES	1250 V	
Gate to emitter voltage VGES	+/- 30 V	
Collector current IC	Tc = 25 °C	50 A, 80A, 150A
	Tc = 100 °C	25 A, 40A      75A
Junction temperature Tj	175 °C	
Collector to emitter saturation voltage VCE(sat)	2.1 V	
Gate to emitter cutoff voltage VGE (off)	5.0 - 6.8 V	
Package Information	TO-247      TO-247 plus	

(Remarks) All registered trademarks or trademarks are the property of their respective owners.